

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Alessandro Callegari, et al.

Examiner: Unassigned

Serial No: Unassigned

Art Unit: Unassigned

Filed: Herewith

Docket: YOR920000447US2 (13796A)

For: METHOD OF FILM DEPOSITION,
AND FABRICATION OF STRUCTURES

Date: September 30, 2003

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with 37 C.F.R. §§1.56, 1.97 and 1.98, it is respectfully requested that the following references, which are also listed on the attached form PTO-1449, be made of record in the above-identified patent application.

1. U.S. Patent No. 6,312,565, issued November 2001 to Misra, et al.;
2. U.S. Patent No. 6,037,003, issued March 14, 2000 to Gordon, et al.;
3. U.S. Patent No. 5,728,222, issued March 17, 1998 to Barbee, et al.;

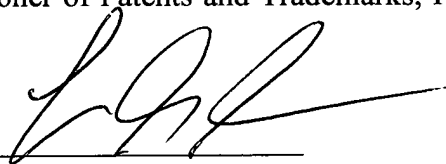
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I hereby certify that this correspondence is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 C.F.R. §1.10 on the date indicated above and is addressed to the Commissioner of Patents and Trademarks, P.O. Box 1450, Alexandria, VA 22313-1450.

Dated: September 30, 2003



Leslie S. Szivos

4. U.S. Patent No. 5,648,113, issued July 15, 1997 to Barbee, et al.;
5. U.S. Patent No. 5,540,777, issued July 30, 1996 to Barbee, et al.;
6. U.S. Patent No. 5,431,734, issued July 11, 1995 to Chapple-Sokol, et al.;
7. U.S. Patent No. 4,097,314, issued June 27, 1978 to Schlesier, et al.;
8. Eble, R., et al., "Low Temperature Aluminum Oxide Deposition Using Trimethylaluminum", Journal of Electronic Materials, Vol. 12, No. 3, pp. 587-601, (1983);
9. Kim, J.S., et al., "Fabrication of Aluminum Oxide Thin Films by a Low-Pressure Metalorganic Chemical Vapor Deposition Technique", App. Phys. Lett., 62(7), February 15, 1993;
10. Fournier, J., et al., "Preparation and Characterization of Thin Films of Alumina by Metal-Organic Chemical Vapor Deposition", Mat. Res. Bull., Vol. 23, pp. 31-36, 1988;
11. Klein, T.M., et al., "Evidence of Aluminum Silicate Formation During Chemical Vapor Deposition of Amorphous Al_2O_3 Thin Films on Si(100)", Applied Physics Letters, Vol. 75, No. 25, pp. 4001-4003, 1999;
12. Lo, S.-H, et al., "Quantum-Mechanical Modeling of Electron Tunneling Current from the Inversion Layer of Ultra-Thin-Oxide nMOSFET's", IEEE Electron Device Letters, Vol. 18, No. 5, pp. 209-211, May 1997;
13. Mutoh, H., et al., "Multilayer Metallization with Planar Interconnect Structure Utilizing CVD Al_2O_3 Film", J. Electrochem.Soc.: SOLID-STATE SCIENCE AND TECHNOLOGY, Vol. 12, No. 7, pp. 987-992, July 1975; and
13. Yom, S.S., et al., "Growth of $\gamma\text{-Al}_2\text{O}_3$ Thin Films on Silicon by Low Pressure Metal-Organic Chemical Vapour Deposition", Elsevier Sequoia, 213, PP. 72-75, 1992.

Pursuant to 37 C.F.R. §1.98(d), copies of the references listed on the enclosed Form PTO-1449 are not provided since they were previously made of record in parent application Serial No. 09/676,882 filed September 29, 2000. The references were cited in the Information

Disclosure Statement filed concurrently with the application on September 29, 2000 and on Form PTO-892 of the Office Action dated October 23, 2002

Consideration of this Information Disclosure Statement is respectfully requested, since the information provided herewith may be material to the examination of the present application as defined under 37 C.F.R. §1.56. This statement is not intended to represent that a search has been performed or that no other art than that identified herein exists.

The instant Information Disclosure Statement is being submitted concurrent with the filing of the present application. Therefore, this filing is made under 37 C.F.R. §1.97(b)(1). An Information Disclosure Statement filed under 37 C.F.R. §1.97(b)(1) requires neither certification nor fee.

Respectfully submitted,



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Registration No. 39,394

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Garden City, New York 11530

LSS:jy:jf

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				ATTY DOCKET NO. YOR920000447US2 (13796A)		SERIAL NO. Unassigned	
				Alessandro Callegari, et al.			
				FILING Herewith		GROUP Unassigned	

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		5,312,565	11/01	Misra, et al.			
		6,037,003	3/14/00	Gordon, et al.			
		5,728,222	3/17/98	Barbee, et al.			
		5,648,113	7/15/97	Barbee, et al.			
		5,540,777	7/30/96	Barbee, et al.			
		5,431,734	7/11/95	Chapple-Sokol, et al.			
		4,097,314	6/27/78	Schlesier, et al.			

FOREIGN PATENT DOCUMENTS								
*	EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>			
			<u>Eble, R., et al., "Low Temperature Aluminum Oxide Deposition Using Trimethylaluminum", <i>Journal of Electronic Materials</i>, Vol. 12, No. 3, pp. 587-601 (1983);</u>
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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			Lo, S.-H, et al., "Quantum-Mechanical Modelling of Electron Tunneling Current From the Inversion Layer of Ultra-Thin-Oxide nMOSFET's", <u>IEEE Electron Device Letters</u> , Vol. 18, No. 5, pp. 209-211, May 1997;
			Mutoh, H., et al., "Multilayer Metallization with Planar Interconnect Structure Utilizing CVD Al ₂ O ₃ Film", <u>J. Electrochem. Soc.: SOLID-SCIENCE AND TECHNOLOGY</u> , Vol. 12, No. 7, pp. 987-992, July 1975; and

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